IN THE SPECIFICATION

Please amend the paragraph spanning page 2 – page 3 as follows:

--A variety of semiconductor integrated circuits use passive filtering techniques that employ capacitors, inductors and resistors. In some cases, active filters using those elements are used as well, such as in a circuit that contains an operational amplifier. Yet, despite the trend toward monolithic integration of different IC functions, passive (RLC) elements generally have not been monolithically integrated (on a single-function IC, nor on a multi-function IC) because, in part, there have been no fabrication techniques for providing these elements in a manner that is well ~~suite~~suited for such integration. For instance, not only should the fabrication technique advantageously be compatible with processing of other structures present on the IC<, but also the passive elements provided should advantageously be compact and easily integrated with the structures and/or devices present on the IC.--

Please amend the paragraph spanning page 9 – page 10 as follows:

--As will be understood by those skilled in the art, a passive transmission line device according to the present invention conductively couples two nodes of a circuit, and each node may be connected to one or more of a variety of circuit elements or signals, including for example, a terminal of an active device (e.g., a transistor), a terminal of a passive device (e.g., a capacitor, resistor, inductor, or another passive transmission line element according to the present invention), a terminal of a power source (e.g., supply voltage, or ground), or a terminal of a conventional interconnect [i.e., a highly conductive transmission line (line), also referred to in the art as a conductive runner (runner)]. Those skilled in the ~~art5~~art will also understand that while various implementations of the present invention may appear geometrically similar to a conventional interconnect at least to the extent that they may both include a narrow conductive line, such ~~geomet5ric~~geometric embodiments of a passive transmission line element according to the present invention nevertheless differ substantially not only structurally but also functionally from a conventional interconnect. As will be better understood from the ensuing description, compared to a conventional highly conductive interconnect, a passive transmission line device according to the present invention has enhanced capacitance (e.g., distributed capacitance, capacitance per unit length) and/or enhanced inductance (e.g., self-inductance, distributed inductance, or inductance per unit length). In combination with the enhanced capacitance and/or enhanced inductance, a passive transmission line device according to the present invention may additionally (optionally) have enhanced resistance (e.g., resistance per unit length). Enhanced inductance is provided by embedding and/or covering the conductive line in a high permeability material. Similarly, embedding and/or

covering the conductive line in a high permitivity material provides enhanced capacitance. Using a resistive material for the conductive line provides enhanced resistance.--

Please amend the paragraph spanning page 12 – page 13 as follows:

--Upon the structure shown in FIG. 1A, a recess dielectric 20, typically composed of silicon dioxide (i.e., ~~Sio2~~SiO_2), silicon nitride (i.e., ~~Si3N4~~Si_3N_4), or another insulator such as those mentioned for first insulating layer 12, is then deposited by standard methods, such as CVD, PVC, or spin coating. Photolithography and wet or dry etching (preferably dry for small feature sizes and high aspect ratios) are then used to define and open recesses (also referred to herein as grooves or trenches) in recess dielectric 20. FIG. 1B shows a recess 22 and a recess 24. Recess 22 has a bottom surface 22B that comprises the top surface of conductive plug 16 and a portion of the top surface of first insulating layer 12 that surrounds plug 16. Recess 24 has a bottom surface 24B that overlies a portion of first insulating layer 12 only. Both recess 22 and 24 have sidewalls 22A and 24A, respectively, formed from first insulating layer 12. As may be appreciated, the recesses extend in the plane perpendicular to the cross-sections depicted in the FIGS. 1A-1H, and the layout of the recesses corresponds to the pathways intended for the passive transmission line devices. Thus, for example, recesses 22 and 24 may represent cross-sectional portions of recesses for two distinct (i.e., not electrically continuous) passive transmission line elements, or for the same (i.e., conductively continuous) passive transmission line element (e.g., the passive transmission line element may be in the form of a loop, coil, or meander).--